



Claim 4 (original)                      4.        A curing light as recited in claim 1 wherein at least one of said epitaxial layers includes a material from the group consisting of GaN, AlGaIn, and InGaIn.

Claim 5 (original)                      5.        A curing light as recited in claim 1 wherein said well has a reflective wall that includes a material selected from the group consisting of Al, Au, Ag, Zn, Cu, Pt, chrome, metal, plating and plastic, said well wall being capable of reflecting light of a wavelength produced by said chip.

Claim 6 (original)                      6.        A curing light as recited in claim 1 wherein said semiconductor chip is selected from the group consisting of light emitting diode chips, laser chips, light emitting diode chip array, diode laser chips, diode laser chip array, surface emitting laser chips, edge emitting laser chips, and VCSEL chips.

Claim 7 (original)                      7.        A curing light as recited in claim 1 wherein said chip is held in place in said well by use of an adhesive selected from the group consisting of heat conductive adhesive and light reflective adhesive.

Claim 8 (original)                      8.        A curing light as recited in claim 1 further comprising a secondary heat sink, said secondary heat sink being affixed to said heat sink, and said secondary heat sink being capable of assisting in dissipation of heat produced by said chip.

Claim 9 (previously cancelled).

Please amend claim 10 as follows:

Claim 10 (currently amended)                      10.        A curing light as recited in claim 8 ~~claim 9~~ further comprising a switch on said wand for initiating emission of light from said semiconductor chip.

Claim 11 (original)                      11.        A curing light as recited in claim 1 further comprising a

cover that provides protective covering for said semiconductor chip and which permits light emitted by said semiconductor chip to substantially pass through it.

Claim 12 (original)                      12.     A curing light as recited in claim 11 wherein said cover is selected from the group consisting of windows and focus lenses.

Claim 13 (original)                      13.     A curing light as recited in claim 8 wherein said secondary heat sink is elongate in shape.

Please amend claim 14 as follows:

Claim 14 (currently amended)                      14.     A curing light comprising:  
          a handpiece,  
          a longitudinal axis of said handpiece,  
          a primary heat sink capable of dissipating heat created by a semiconductor light source,  
          a well in said heat sink, said well being sized to receive a semiconductor chip capable of producing light that is useful in curing light-curable materials,  
          a top opening of said well,  
          a bottom of said well,  
          a wall of said well, said wall of said well being capable of reflecting light,  
          a semiconductor chip capable of producing light that is useful in curing light-curable materials,  
          said semiconductor chip having a substrate,  
          said substrate being selected from the group consisting of Si, GaAs, GaN, InP, sapphire, SiC, GaSb, and InAs,  
          said semiconductor chip having a plurality of epitaxial layers,  
          a contact layer as one of said epitaxial layers, said contact layer serving to establish an electrical contact for said chip,  
          a cladding layer as one of said epitaxial layers,  
          an active layer as one of said epitaxial layers, said active layer serving to allow electrons

jump from a conduction band to valance and emit energy which converts to light, and  
a buffer layer as one of said epitaxial layers,  
at least some of said light produced by said chip being emitted from said well at an  
angular orientation  $\theta$  with respect to said handpiece longitudinal axis, said angle  $\theta$  being in the  
range of from about 30 degrees to about 150 degrees.

Claim 15 (original) 15. A curing light as recited in claim 14 wherein at least one of said  
epitaxial layers includes a material from the group consisting of GaN, AlGa<sub>N</sub>, and InGa<sub>N</sub>.

Claim 16 (original) 16. A curing light as recited in claim 14 wherein said well has a  
reflective wall that includes a material selected from the group consisting of Al, Au, Ag, Zn, Cu,  
Pt, chrome, metal, plating and plastic, said well wall being capable of reflecting light of a  
wavelength produced by said chip.

Claim 17 (original) 17. A curing light as recited in claim 14 wherein said chip is held in  
place in said well by use of an adhesive selected from the group consisting of heat conductive  
adhesive and light reflective adhesive.

Claim 18 (original) 18. A curing light as recited in claim 14 further comprising a  
secondary heat sink, said secondary heat sink being affixed to said heat sink, and said  
secondary heat sink being capable of assisting in dissipation of heat produced by said chip.

Please amend claim 19 as follows:

Claim 19 (currently amended) 19. A curing light comprising:  
a housing for containing components of the curing light,  
a longitudinal axis of said housing,  
~~a handpiece of manipulation and applying light from the curing light to a light curable~~  
~~material,~~  
~~electronic circuitry for controlling the curing light,~~

a primary heat sink capable of dissipating heat created by a semiconductor light source,  
a semiconductor chip capable of producing light that is useful in curing light-curable materials,

said semiconductor chip being affixed to said primary heat sink by use of an adhesive,  
said semiconductor chip having a substrate,

said substrate being selected from the group consisting of Si, GaAs, GaN, InP, sapphire, SiC, GaSb, and InAs,

said semiconductor chip having a plurality of epitaxial layers,

a contact layer as one of said epitaxial layers, said contact layer serving to establish an electrical contact for said chip,

a cladding layer as one of said epitaxial layers,

an active layer as one of said epitaxial layers, said active layer serving to allow electrons jump from a conduction band to valance and emit energy which converts to light, and

a buffer layer as one of said epitaxial layers;

wherein at least one of said epitaxial layers includes a material from the group consisting of GaN, AlGaIn, and InGaIn; and

wherein at least some light directly emitted by said semiconductor chip is emitted forward from the semiconductor chip at an angular orientation  $\theta$  with respect to said longitudinal axis, said angle  $\theta$  being in the range of from about 30 degrees to about 150 degrees.

[cl020] 20. A curing light as recited in claim 19 further comprising a secondary heat sink, said secondary heat sink being affixed to said heat sink, and said secondary heat sink being capable of assisting in dissipation of heat produced by said chip.